



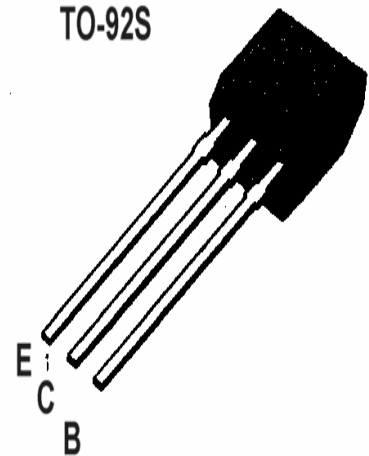
《风光欣》技术资料

2SA1585S

PNP EPITAXIAL SILICON TRANSISTOR

ABSOLUTE MAXIMUM RATINGS(TA=25)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V _{CB0}	-20	V
Collector-Emitter Voltage	V _{CEO}	-20	V
Emitter -Base Voltage	V _{EBO}	-6	V
Collector Current	I _c	-2	A
Collector Dissipation	P _c	0.4	W
Junction Temperature	T _J	150	
Storage Temperature	T _{STG}	-55 ~150	



ELECTRCAL CHARACTERISTICS(TA=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV _{CB0}	I _c = -50 μ A, I _E =0	-20			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _c = -1mA, I _B =0	-20			V
Emitter -Base Breakdown Voltage	BV _{EBO}	I _E = -50 μ A, I _c =0	-6			V
Collector Cut-off Current	I _{CB0}	V _{CB} = -20V, I _E =0			-100	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} = -5V, I _c =0,			-100	nA
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _c = -2A, I _B =-0.1A			-0.5	V
DC Current Gain	h _{FE}	V _{CE} = -2V, I _c =-100mA,	120		390	
Transition ftequency	f _T f=100MHz	V _{CE} = -2V, I _E = -500mA		240		MHZ
Output Capacitance	C _{OB}	V _{CB} = -10V, I _E = 0, f=1MHZ		35		pF

h_{FE} CLASSIFICAT ION

Ltem	Q	R	S
H _{FE}	120-270	180-390	270-560